



18N65F

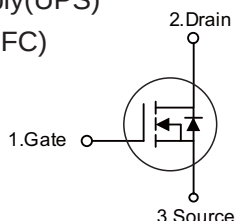
N-Channel Enhancement Mode MOSFET

Features

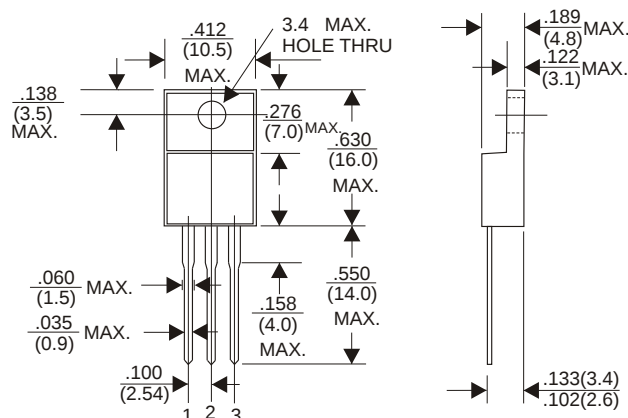
- 650V,18A
- $R_{DS(ON)} = 0.41\Omega$ (Typ.) @ $V_{GS} = 10V$, $I_D = 9A$
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)



ITO-220F (FULLY INSULATED)



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	650	V
V_{GSS}	Gate-Source Voltage	± 30	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ\text{C}$ 18	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C = 25^\circ\text{C}$ 72	A
I_D	Continuous Drain Current($V_{GS} = 10V$)	$T_C = 25^\circ\text{C}$ 18	A
		$T_C = 100^\circ\text{C}$ 11.5	
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$ 260	W
		$T_C = 100^\circ\text{C}$ 104	
R_{JC}	Thermal Resistance-Junction to Case	0.48	$^\circ\text{C/W}$
R_{JA}	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C/W}$
Drain-Source Avalanche Ratings			
E_{AS}	Avalanche Energy, Single Pulsed	500	mJ

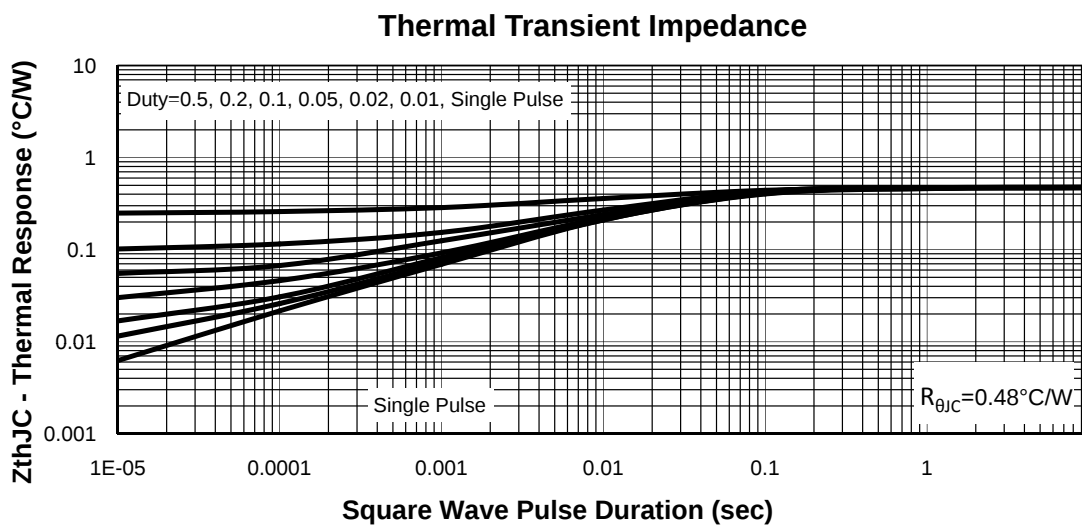
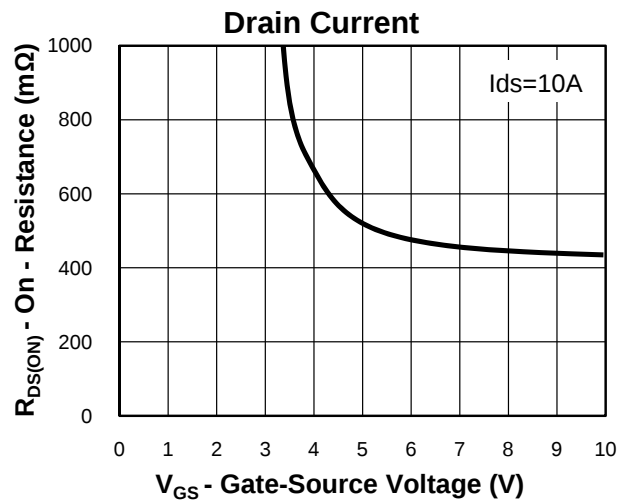
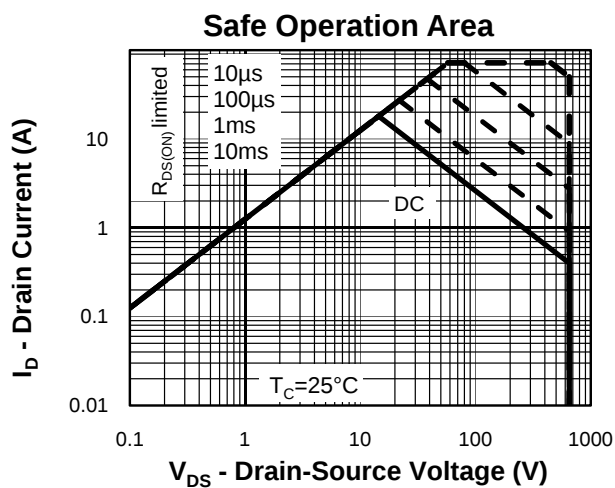
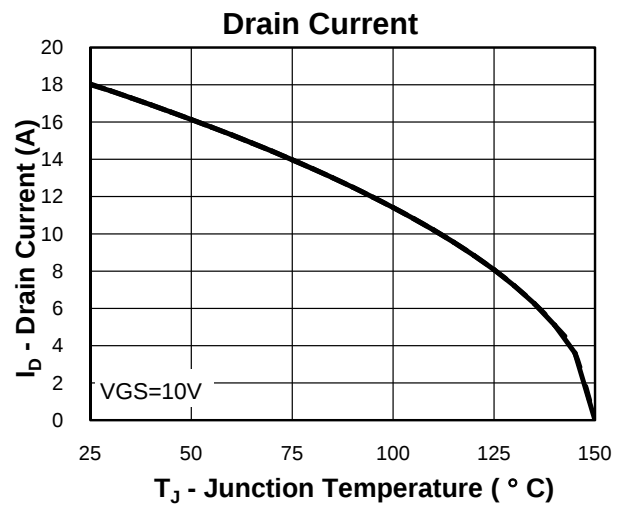
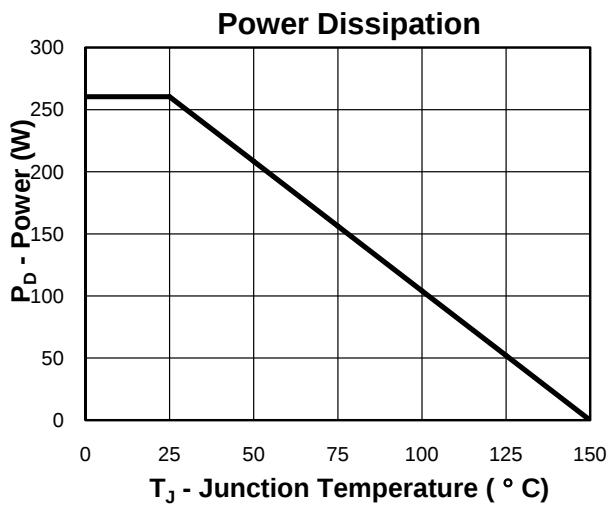
18N65F

Electrical Characteristics (T =25 unless otherwise specified)

Symbol	Parameter	Test Condition	18N65F			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	650			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	3		5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±30V, V _{DS} =0V			±100	nA
R _{DS(ON)}	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =10A		410	500	mΩ
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _{SD} =10A, V _{GS} =0V			1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =18A, dI _{SD} /dt=100A/μs		560		ns
Q _{rr}	Reverse Recovery Charge			4.3		μC
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		2.8		Ω
C _{iSS}	Input Capacitance	V _{GS} =0V, V _{DS} =300V, Frequency=1.0MHz		4350		pF
C _{oSS}	Output Capacitance			410		
C _{rSS}	Reverse Transfer Capacitance			110		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =300V, R _L =100Ω, I _{DS} =18A, V _{GEN} =10V, R _G =4.7Ω		47		ns
t _r	Turn-on Rise Time			81		
t _{d(OFF)}	Turn-off Delay Time			95		
t _f	Turn-off Fall Time			52		
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =520V, V _{GS} =10V, I _{DS} =18A		128		nC
Q _{gs}	Gate-Source Charge			43		
Q _{gd}	Gate-Drain Charge			52		

Notes: Pulse width limited by safe operating area.
 Calculated continuous current based on maximum allowable junction temperature.
 Limited by T_{Jmax} , $I_{AS}=10A$, $V_{DD}=100V$, $R_G=50\Omega$, Starting $T_J=25^{\circ}C$.
 Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 Guaranteed by design, not subject to production testing.

RATING AND CHARACTERISTIC CURVES (18N65F)



RATING AND CHARACTERISTIC CURVES (18N65F)

